NSN 5962-01-306-0384

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Body Length:	
0.840 inches	
Body Width:	
0.310 inches	
Body Height:	
0.185 inches	
Maximum Power Dissipation Rating:	
739.0 milliwatts	
Operating Tempurature Range:	
-55.0/+125.0 degrees celsius	
Storage Tempurature Range:	
-65.0/+150.0 degrees celsius	
Features Provided:	
Monolithic and bipolar and schottky and programmable and w/active pull-up	
Inclosure Material:	
Ceramic	
Inclosure Configuration:	
Dual-in-line	
Output Logic Form:	
Transistor-transistor logic	
Input Circuit Pattern:	
10 input	
Case Outline Source And Designator:	
D-2 mil-m-38510	
Terminal Surface Treatment:	
Solder	
Voltage Rating And Type Per Characteristic:	
7.0 volts power source	
Time Rating Per Chacteristic:	
35.00 nanoseconds propagation delay time, low to high level output and 35.00 nanoseconds propagation de	alay time, high to low level
output	
Memory Device Type:	
Rom	
Test Data Document:	
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards,	etc.).
Terminal Type And Quantity:	
16 printed circuit	
Shelf Life:	
N/a	
Unit Of Measure:	
 Demilitarization:	
Yes - demil/mli	

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